CERAMIC DISC CAPACITORS CHARACTERISTICS

項目 ITEM	規格 SPECIFICATION		檢測方法及條件 TEST METHOD AND CONDITION
7. 焊錫附著性及焊錫耐熱性 Resistance to solder heat and Solder ability of leads	靜電容量變化率 Capacitance Change	T.C.:±5% or ±0.5PF	將元件端子線浸入240℃ ±5℃的溶錫內，端子線浸至離本體邊緣2.0-3.0mm處，并保持3+1/-0秒。試驗前，將元件放置85+3/-0℃中預熱，5分鐘後再進行焊錫試驗；試驗後，元件須放置室溫中24小時後方可進行電氣特性的測試。 The lead wire shall be immersed into the melted solder of 240℃ ±5℃ up to about 2.0 to 3.0 mm from the main body for 3+1/-1 seconds.. Capacitor shall be measured after leaving for 24 hours at room temperature.
		HIK、S.C.: Y5E、Y5P、BN:±10% X7R、Y5R:±15% Y5T、Y5U、Z5U:±20% Z5V、Y5V:±30%	
	Q OR DF	T.C.: ①C<30PF: Q≥400+20xC ②C≥30PF: Q≥1000	
		HIK: ①Y5E、Y5P、X7R、Z5U、Y5U: DF≤2.5% ②Z5V、Y5V: DF≤5% ③BN、Y5T: DF≤0.5%, Y5R: DF≤0.2%	
		S.C.: ①Y5P、Y5U: DF≤5% ②Y5V: Df≤7%	
	絕緣電阻 Insulation Resistance	T.C.:10000M Ω min HIK: 5000M Ω min S.C.: 100M Ω min	
8. 溫度循環 Temp. Cycle	外觀 Appearance	無缺陷 No marked defect	將電容器進行如下五個溫度循環試驗： Capacitor shall be subjected to five cycles of the temperature cycle as follwing: Step / Temp.(℃) / Time 1 / Min rated temp(+0-3) / 30min 2 / 25 / 30min 3 / Max rated temp(+0-3) / 30min 4 / 25 / 30min 放置室溫下一段時間再測量其電氣特性： Measure at room temperature after cooling for: T.C.:24Hr HIK、S.C.:48Hr
	靜電容量 Capacitance	T.C.:±5% or ±0.5PF max. HIK、(S.C.): Y5E、Y5P、BN:±10%; X7R、Y5R:±15%; Y5T、Y5U、Z5U:±20%; Z5V、Y5V:±30%。	
	Q OR DF	T.C.: C<30PF: Q≥400+20xC C≥30PF: Q≥1000 HIK Y5E、Y5P、X7R、Y5U、Z5U DF≤5% Y5V、Z5V DF≤7.5% BN、Y5T DF≤1% Y5R DF≤0.5% S.C. Y5P、Y5U DF≤7.5% Y5V DF≤10%	
	絕緣電阻 Insulation Resistance	與初始規格值一致 To satisfy the specified initial value.	
9. 耐濕負荷 Humidity loading	外觀 Appearance	無顯著之異常現象 No marked defect	在溫度40（±2℃）、相對濕度95%的狀態下，連續施加直流額定電壓（充放電電流爲50mA以下）500（+24-0）小時； 試驗後置于室溫中： T.C.類規格需放置24小時以上方可測定其電氣特性； HIK、半導體類規格需放置48小時以上方可測定其電氣特性。 Apply rated voltage for 500(+24-0)hours at 40(±2℃) in 95% RH Charge and discharge current 50mA max. Leave the capacitors in ambient condition for over the following time. Measurement T.C.:24Hrs HIK、S.C.:48Hrs
	靜電容量變化率 Capacitance Change	T.C.:±7.5% or ±0.75PF max.	
		HIK、半導體類 (S.C.): Y5E、Y5P、BN: ±15% X7R、Y5R: ±20% Y5T、Y5U、Z5U: ±25% Z5V、Y5V: ±35%	
	Q OR DF	T.C.: ①C<10PF: Q≥200+10×C ②10PF≤C<30PF: Q≥275+2.5×C ③C≥30PF: Q≥350	
		HIK: Y5E、Y5P、X7R、Y5U、Z5U DF≤5% Y5V、Z5V DF≤7.5% BN、Y5T DF≤1% Y5R DF≤0.5%	
		半導體類(S.C.): Y5P、Y5U DF≤7.5% Y5V Df≤10%	
	絕緣電阻 Insulation resistance	500M Ω min.or 25M Ω XUF min.	